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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
Youichi ISHIMURA, et al. ✓ : EXAMINER: TRAN, T.  
SERIAL NO: 09/881,675 ✓ :  
FILED: JUNE 18, 2001 ✓ : GROUP ART UNIT: 2811  
FOR: FIELD-EFFECT SEMICONDUCTOR :  
DEVICE

#12/B  
Amst  
NTE  
J. McQuinn  
4/3/03

TECHNOLOGY CENTER 2800

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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated January 3, 2003, please amend the above-identified application as follows:

IN THE SPECIFICATION

Page 7, lines 2-17, please amend the paragraph to read as follows:

Fig. 1 is a vertical cross-sectional view that schematically shows the structure of an insulated gate bipolar transistor (abbreviated as IGBT hereafter) in accordance with a first embodiment of the present invention. In this IGBT 10, an n<sup>+</sup>-buffer layer 3 and an n- layer 2 are successively formed on a p<sup>+</sup>-collector layer 4 that consists of a p<sup>+</sup>-semiconductor substrate. Also, a p-base region 6 is formed as part of the upper surface of the n- layer 2. Further, high-density impurities of n type are selectively diffused to form n<sup>+</sup>-emitter regions 7 as part of the upper surface of the p-base region 6. The part of the surface region of the p-base region 6 which is located between the n<sup>-</sup> layer 2 and the n<sup>+</sup>-emitter regions 7 forms a channel

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